

isc N-Channel MOSFET Transistor

IPA60R280E6, IIPA60R280E6

• FEATURES

- Static drain-source on-resistance:
 R_{DS}(on) ≤0.28Ω
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

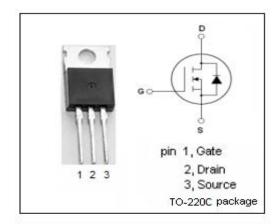
 Provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use

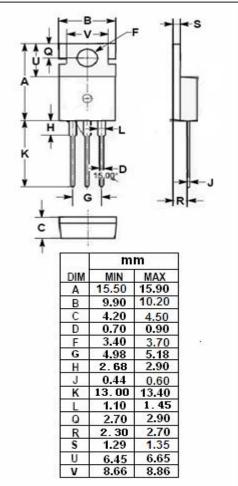


ADOCESTE MAXIMOM (VATINGO)						
SYMBOL	PARAMETER	VALUE	UNIT			
V _{DSS}	Drain-Source Voltage	600	V			
V _{GS}	Gate-Source Voltage	±20	V			
I _D	Drain Current-Continuous	13.8	А			
I _{DM}	Drain Current-Single Pulsed 40		А			
P _D	Total Dissipation @T _c =25℃	c=25°C 104				
Tj	Max. Operating Junction Temperature	action Temperature 150				
T _{stg}	Storage Temperature	-55~150	$^{\circ}$			

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	1.2	°C/W
Rth(ch-a)	Channel-to-ambient thermal resistance	62	°C/W







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =0.25mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =0.43mA	2.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; ID=6.5A			0.28	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V; V _{DS} =0V			0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			1	μА
V _{SD}	Diode forward voltage	I _F =6.5A; V _{GS} = 0V		0.9		V

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